Description

The G3035LA uses advanced trench technology to provide excellent $R_{DS(ON)}$, This device is suitable for use as a load switch or in PWM applications.

AEC-Q101 Qualified

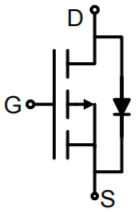
General Features

V_{DSS}	$R_{DS(ON)}$ @-4.5V(Typ)	$R_{DS(ON)}$ @-10V(Typ)	I_D
-30V	60mΩ	48mΩ	-4.1A

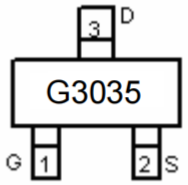
- High power and current handing capability
- RoHS Compliant
- Surface mount package

Application

- PWM applications
- Load switch
- Power management



Schematic diagram



Marking and pin assignment



SOT-23-3

Ordering Information

Part Number	Marking	Case	Packaging
G3035LA	G3035	SOT-23-3	3000pcs/Reel

Absolute Maximum Ratings (T_A=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current-Continuous	I_D	-4.1	A
Drain Current-Pulsed (Note 1)	I_{DM}	-16	A
Maximum Power Dissipation	P_D	1.4	W
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55 To 150	℃

Thermal Characteristic

Thermal Resistance,Junction-to-Ambient (Note 2)	$R_{\theta JA}$	90	℃/W

Electrical Characteristics (T_A=25℃unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=-250μA	-30	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-30V,V_{GS}=0V	-	-	-0.3	μA

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=-250μA	-1	-1.5	-2	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=-10V, I_D=-2.1A	-	48	59	mΩ
		V_{GS}=-4.5V, I_D=-2.1A	-	60	75	mΩ
Forward Transconductance	g_{FS}	V_{DS}=-5V,I_D=-4.1A	5.5	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{lss}	V_{DS}=-15V,V_{GS}=0V, F=1.0MHz	-	650	-	PF
Output Capacitance	C_{oss}		-	105	-	PF
Reverse Transfer Capacitance	C_{rss}		-	65	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=-15V,R_L=3.6Ω V_{GS}=-10V,R_{GEN}=3Ω	-	8.5	-	nS
Turn-on Rise Time	t_r		-	4.5	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	26	-	nS
Turn-Off Fall Time	t_f		-	12.5	-	nS
Total Gate Charge	Q_g	V_{DS}=-15V,I_D=-4A,V_{GS}=-10V	-	12.5	-	nC
Gate-Source Charge	Q_{gs}		-	2.8	-	nC
Gate-Drain Charge	Q_{gd}		-	2.7	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	V_{GS}=0V,I_S=-2A	-	-	-1.2	V

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production

Typical Electrical and Thermal Characteristics

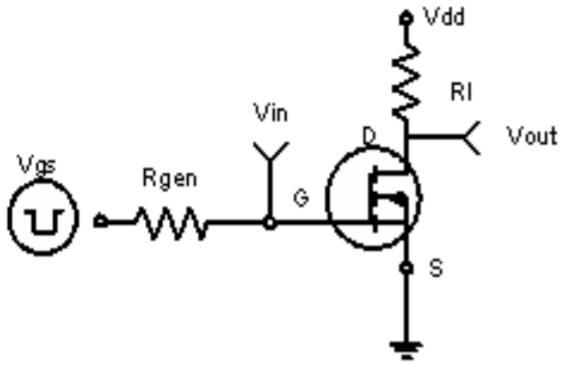


Figure 1:Switching Test Circuit

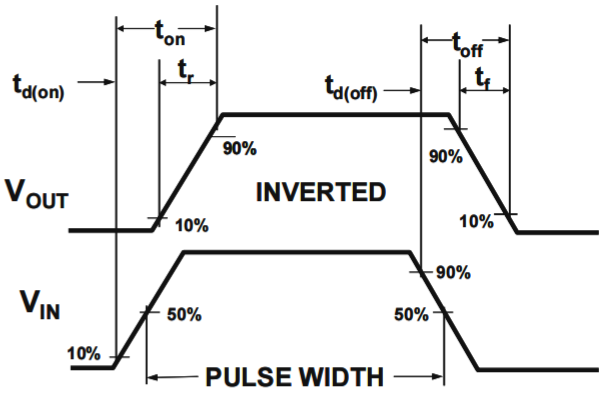


Figure 2:Switching Waveforms

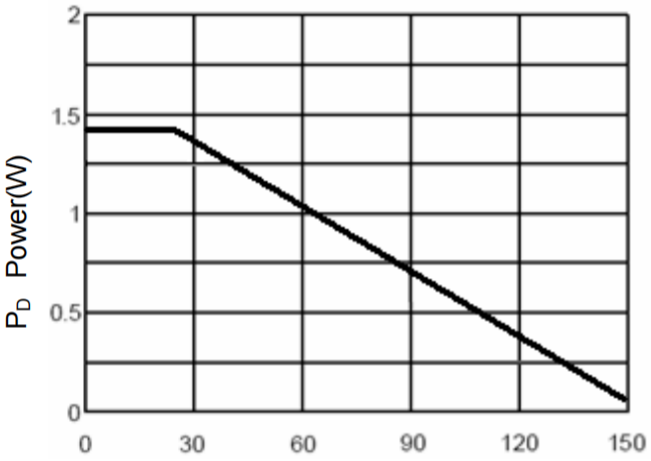


Figure 3 Power Dissipation

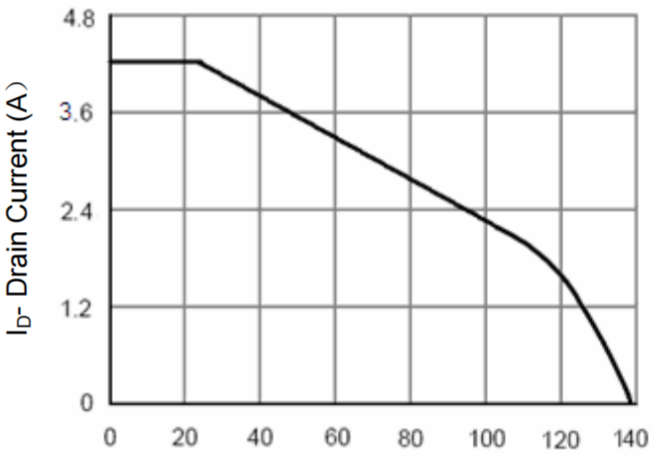


Figure 4 Drain Current

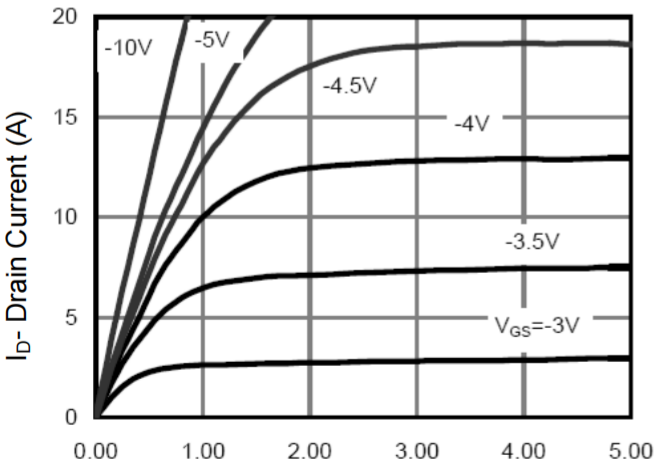


Figure 5 Output Characteristics

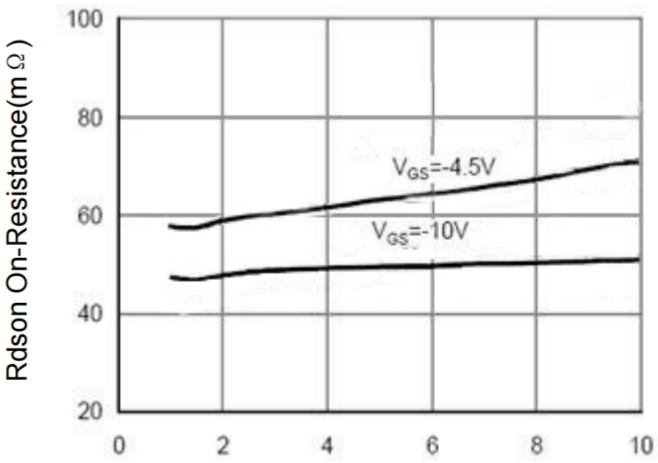


Figure 6 Drain-Source On-Resistance

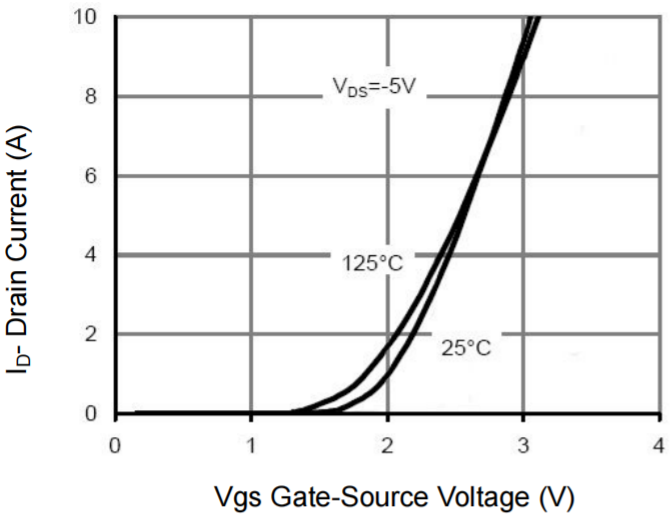


Figure 7 Transfer Characteristics

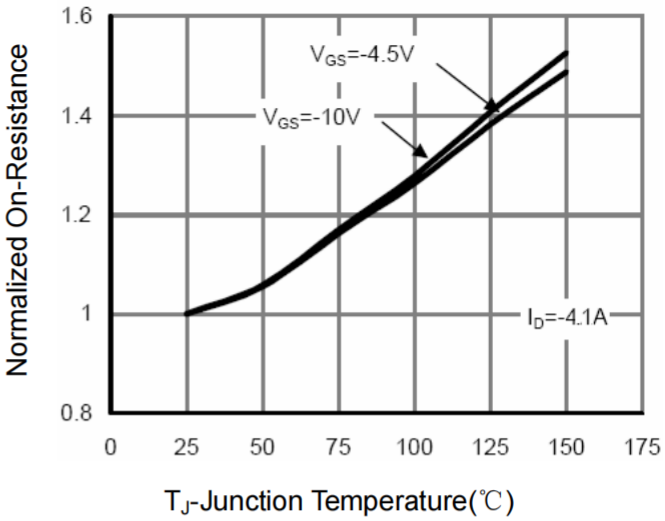


Figure 8 Drain-Source On-Resistance

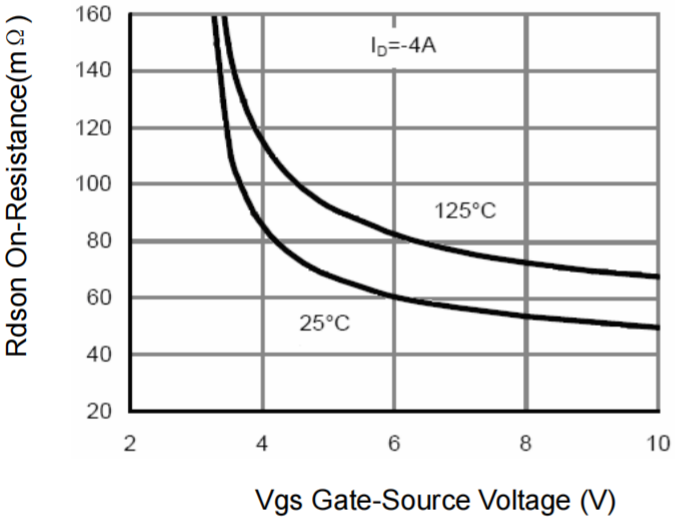


Figure 9 Rdson vs Vgs

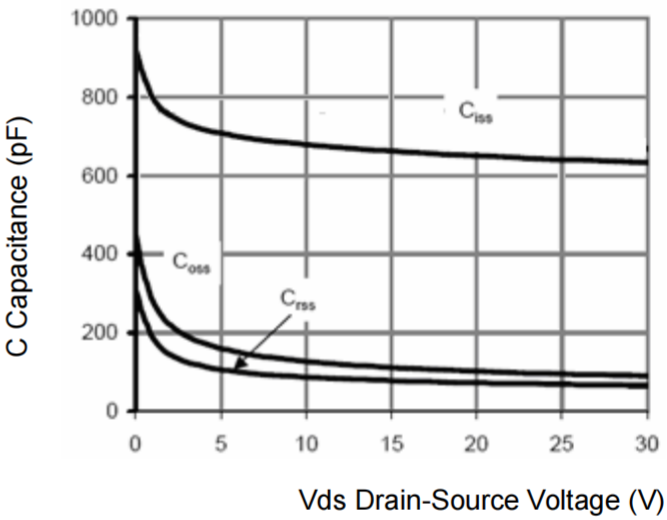


Figure 10 Capacitance vs Vds

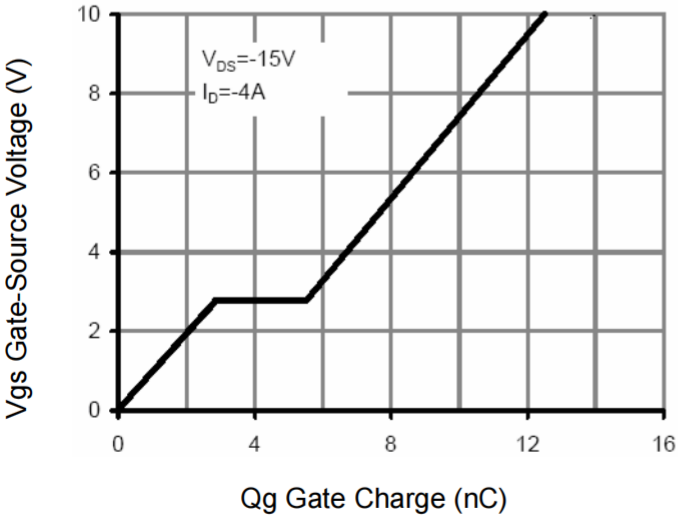


Figure 11 Gate Charge

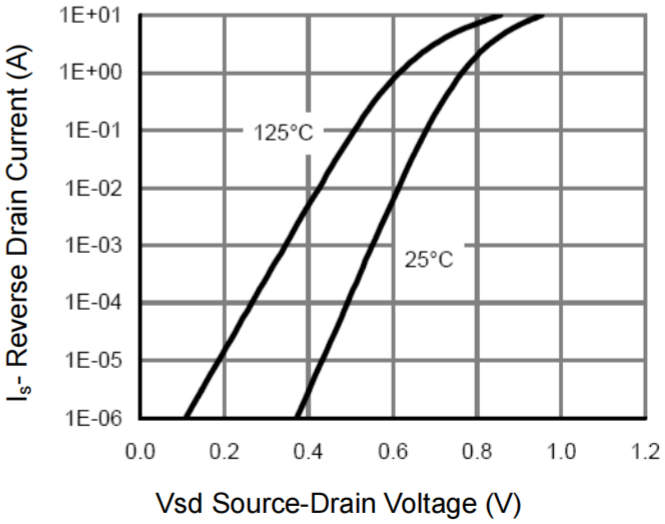


Figure 12 Source- Drain Diode Forward

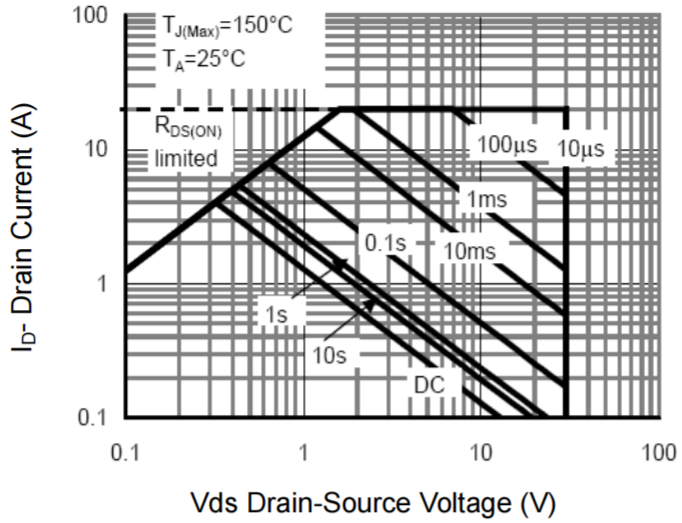


Figure 13 Safe Operation Area

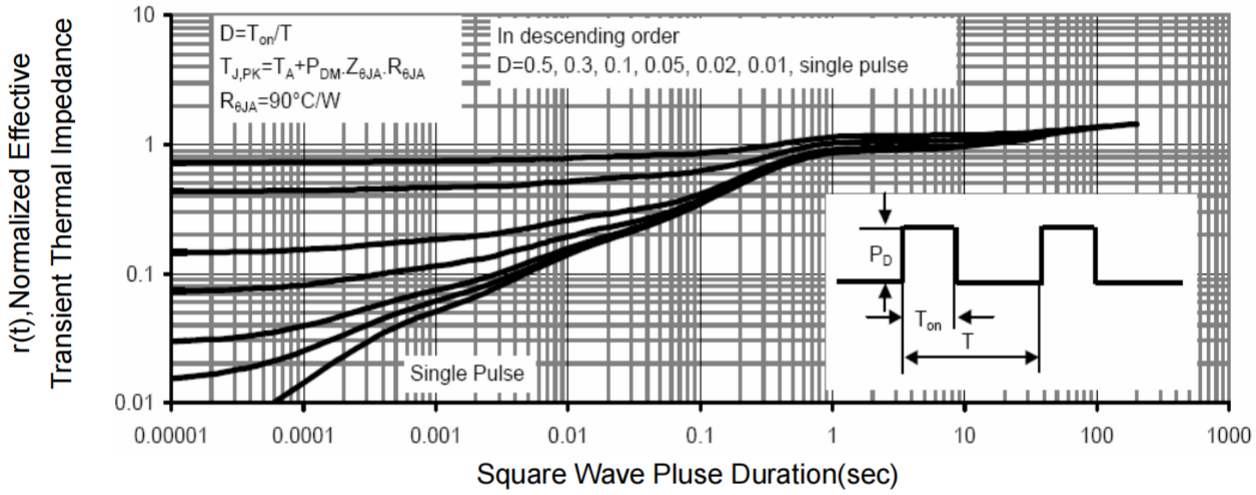
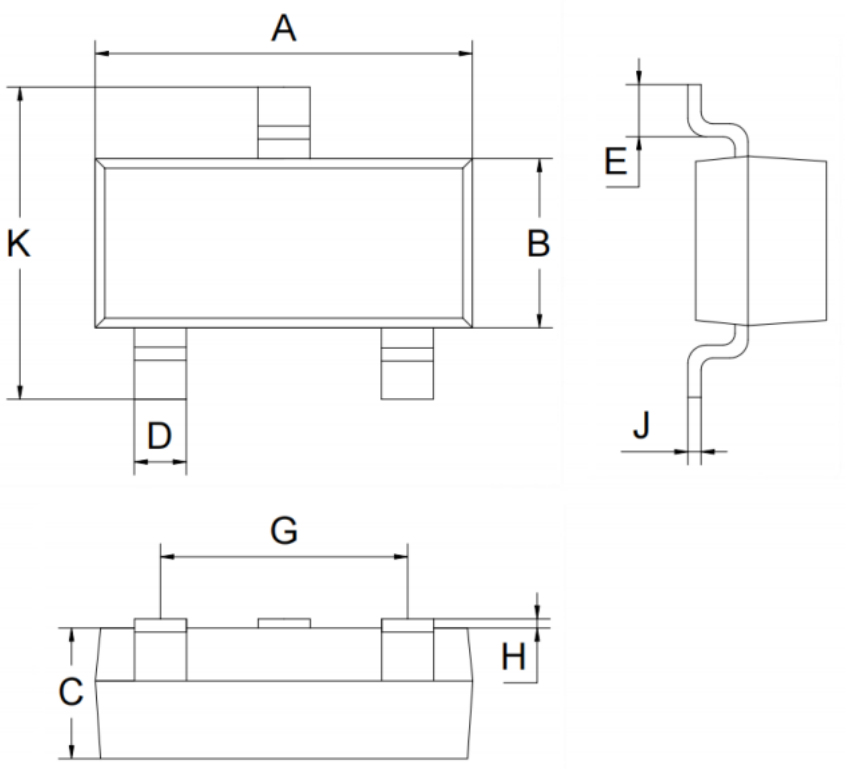


Figure 14 Normalized Maximum Transient Thermal Impedance

SOT-23-3 Package information



SOT-23-3L			
Dim	MIN	NOM	MAX
A	2.80	2.90	3.00
B	1.50	1.60	1.70
C	1.00	1.10	1.20
D	0.30	0.40	0.50
E	0.25	0.40	0.55
G	1.90		
H	0.00	-	0.10
J	0.047	0.127	0.207
K	2.60	2.80	3.00
All Dimensions in mm			